

EE 320 Electronics

Lecture 12

MARCH 11, 2013

Review the test

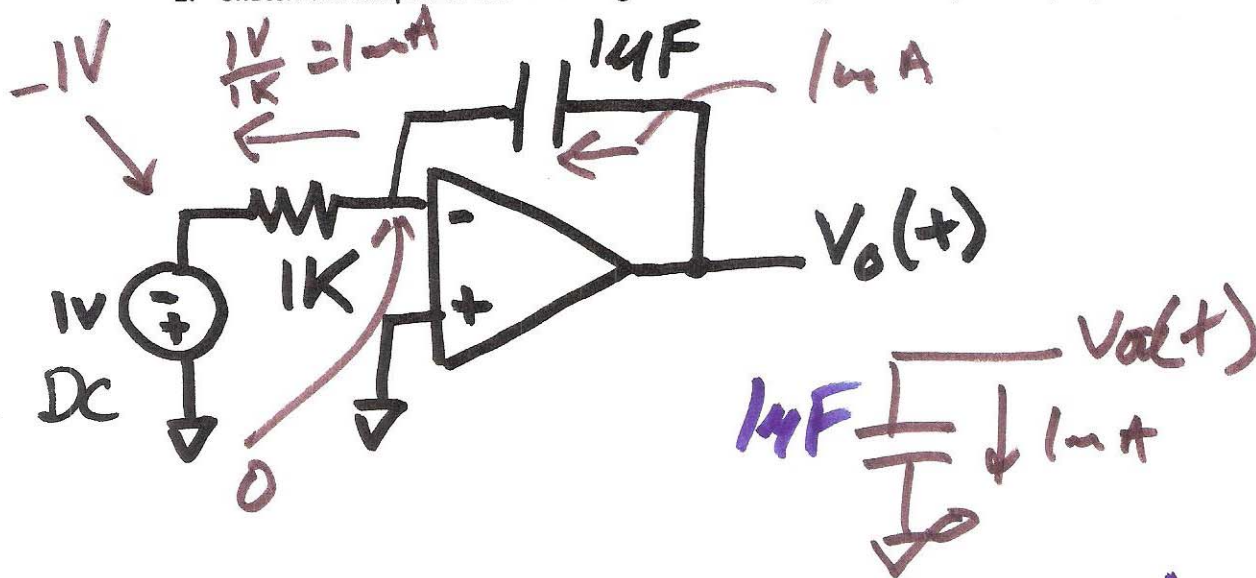
TRANSISTORS

N-channel      metal oxide semiconductor  
P-channel      field effect transistor

MOSFET

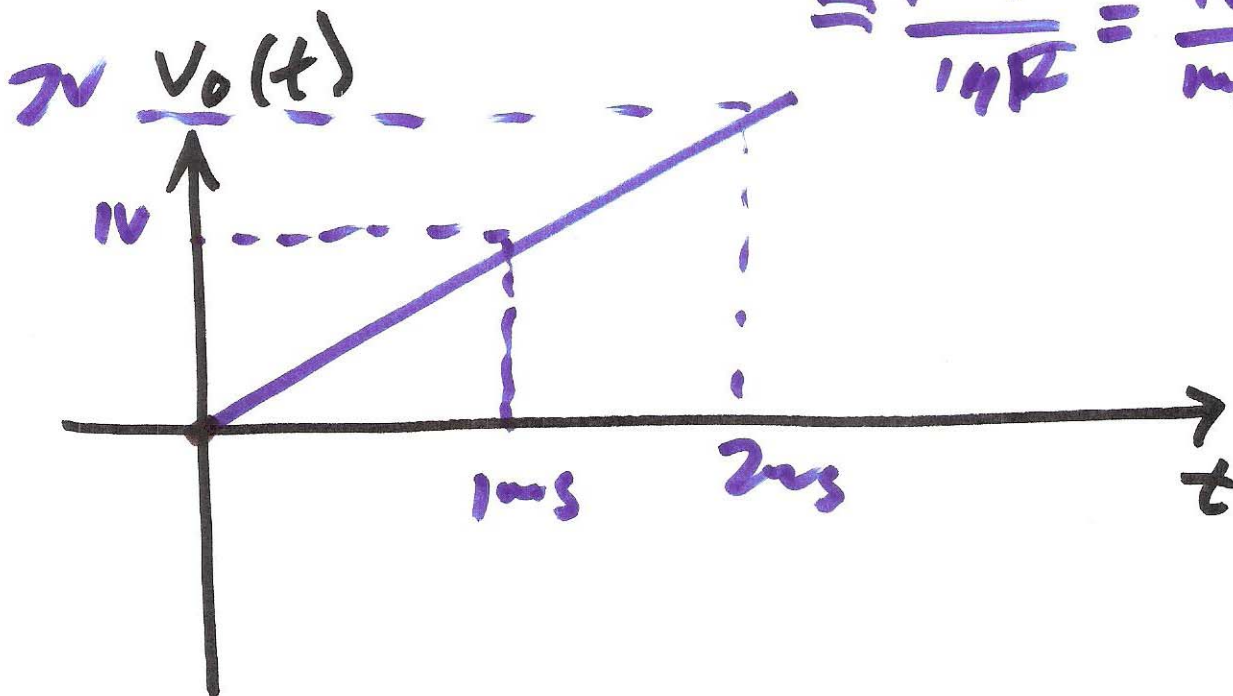
Closed notes, open book, show your work (hand calculations, including algebra) for credit.

1. Sketch the output of the following circuit assuming it's initially at 0V. (15 points)



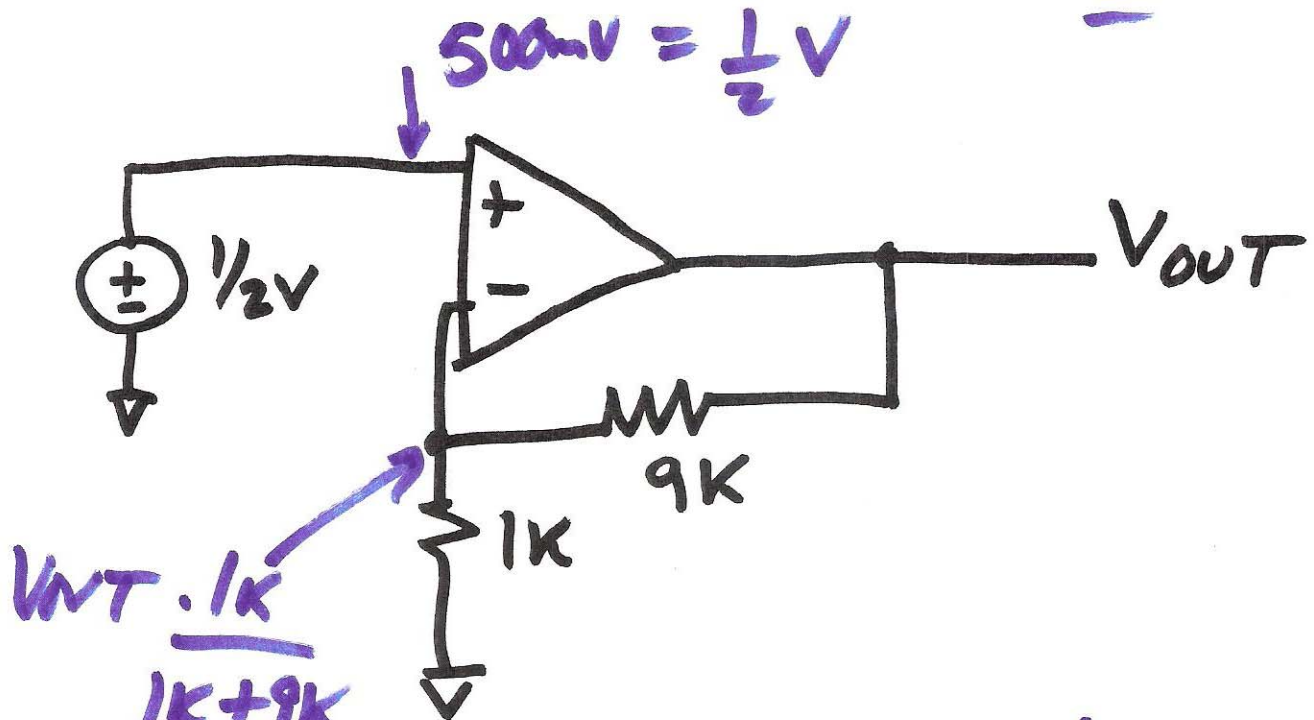
CONST!  $I = C \frac{dV_o}{dt}$

$$= \frac{1mA}{14F} = \frac{1V}{ms} = \frac{dV_o}{dt}$$



§2)

2. Determine the output voltage in the following circuit if the op-amp open-loop gain is 100. (10 points)

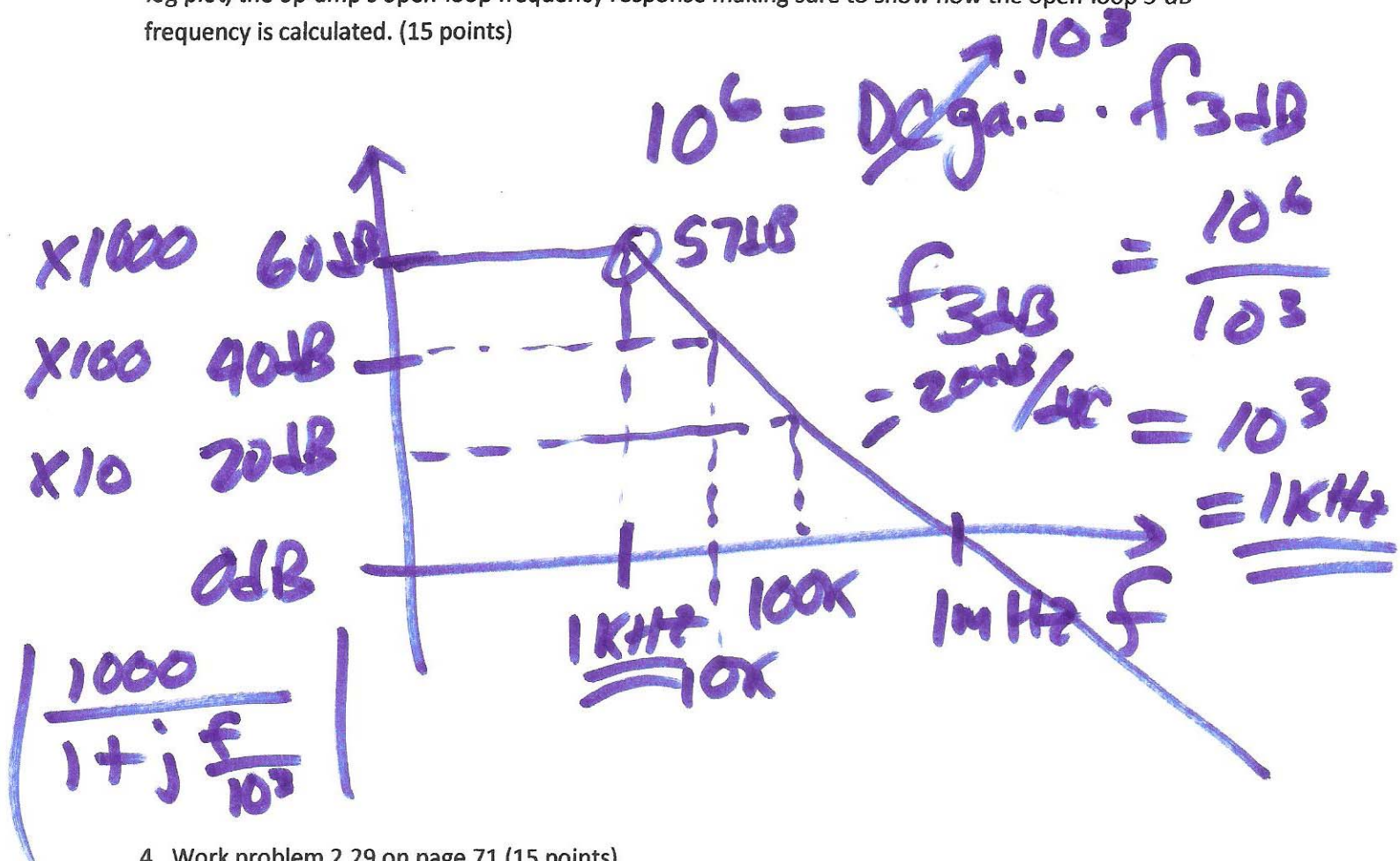


$$V_{INT} = 100 \cdot \left( \frac{1}{2} - \frac{V_{OUT}}{10} \right)$$

$$V_{OUT} = \underline{\underline{4.55V}}$$

2)

3. An op-amp has a unity-gain frequency of 1 MHz and a DC gain of 1,000 (= 60 dB). Sketch, using a log-log plot, the op-amp's open-loop frequency response making sure to show how the open-loop 3-dB frequency is calculated. (15 points)



4. Work problem 2.29 on page 71 (15 points)

3) 4)



5. If Si is doped with Boron having a density of  $10^{16}$  atoms/cm<sup>3</sup> is it n- or p-type? What are n and p assuming  $n_i = 10^{11}$  carriers/cm<sup>3</sup>? What happens to n and p as temperature increases? Why? (15 points)

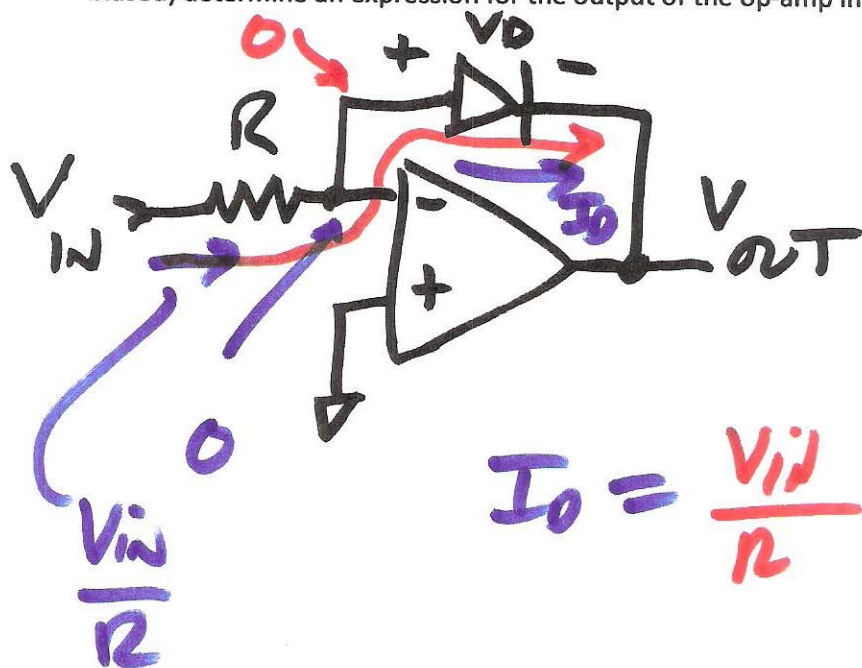
p-type

$$p \approx N_A = 10^{16} \frac{\text{holes}}{\text{cm}^3}$$

$T \uparrow$  p doesn't change

$$T \uparrow \quad n = \frac{n_i^2}{p}, \quad n_i \uparrow$$

6. Assuming the input signal, in the following circuit, is always positive (so that the diode is forward biased) determine an expression for the output of the op-amp in terms of the input. (15 points)

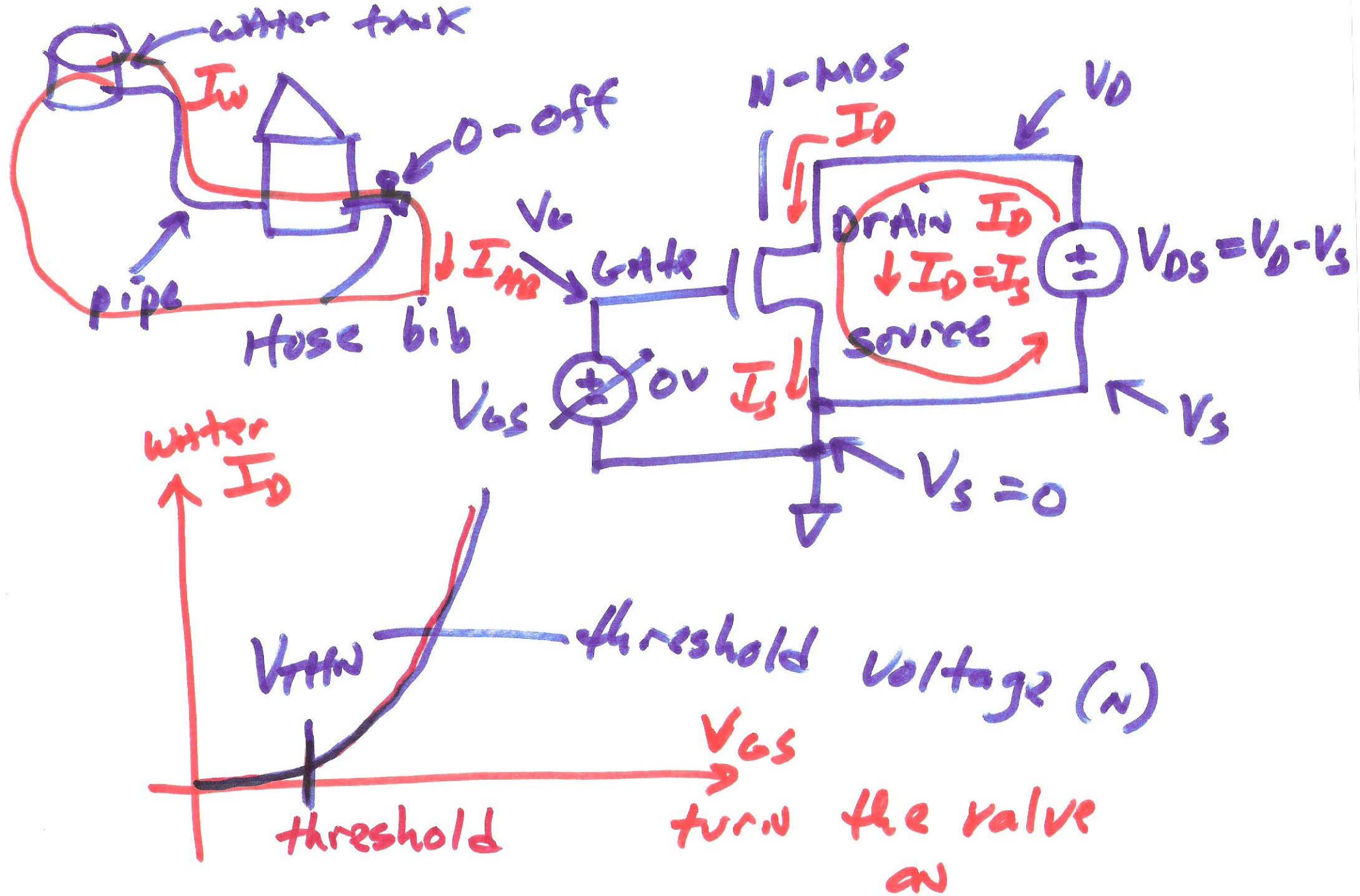


$$I_D = \frac{V_{IN}}{R}$$

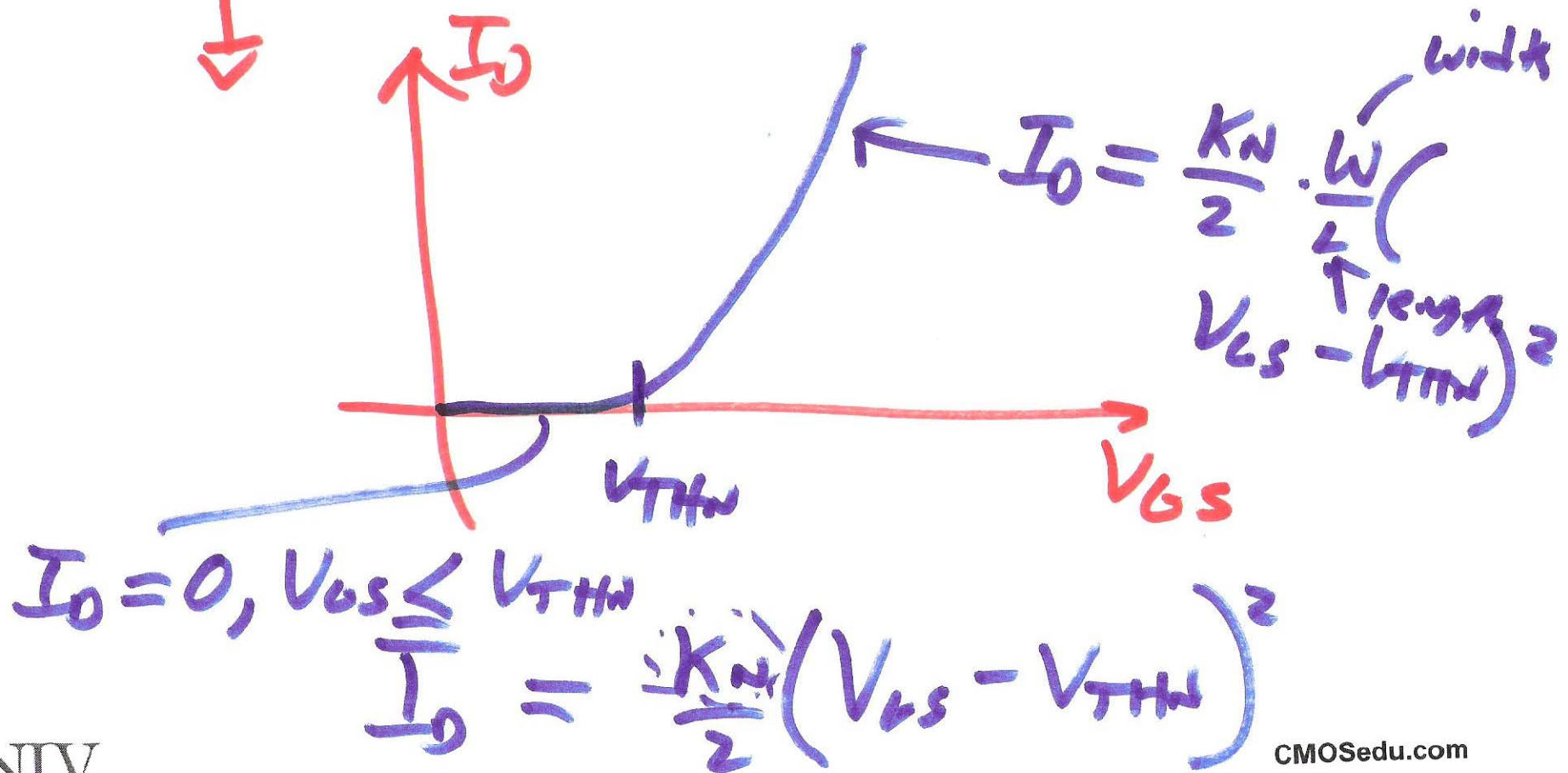
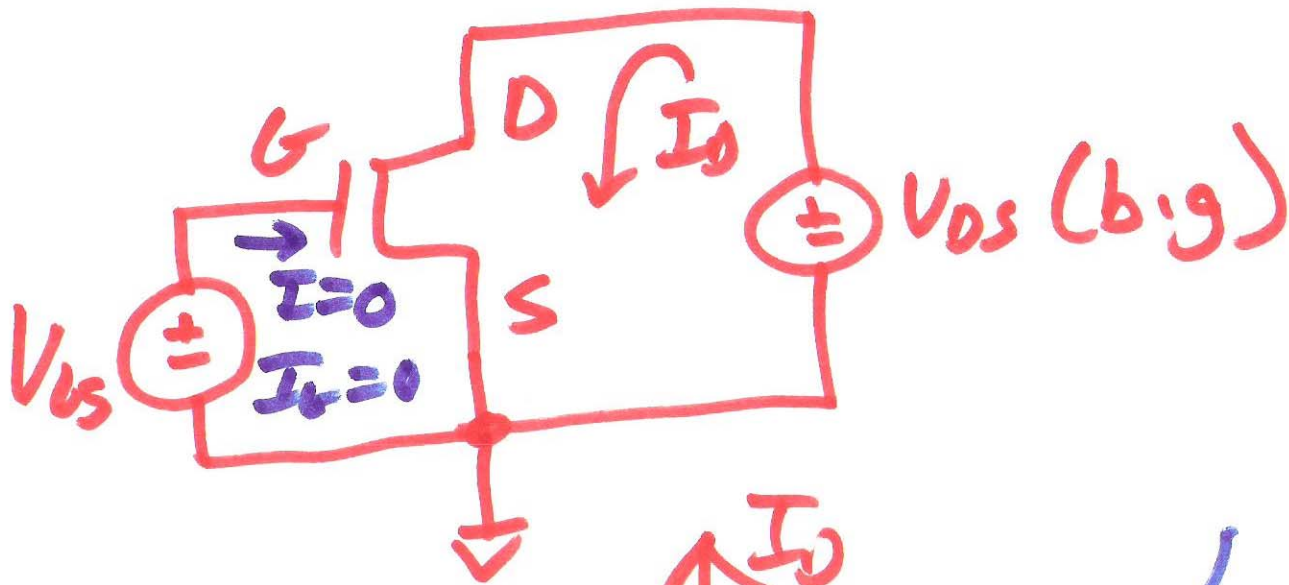
$$V_{OUT} = -V_D$$

$$= -N V_T \ln \frac{I_D}{I_S}$$

$$= -N V_T \ln \frac{V_{IN}}{R \cdot I_S}$$



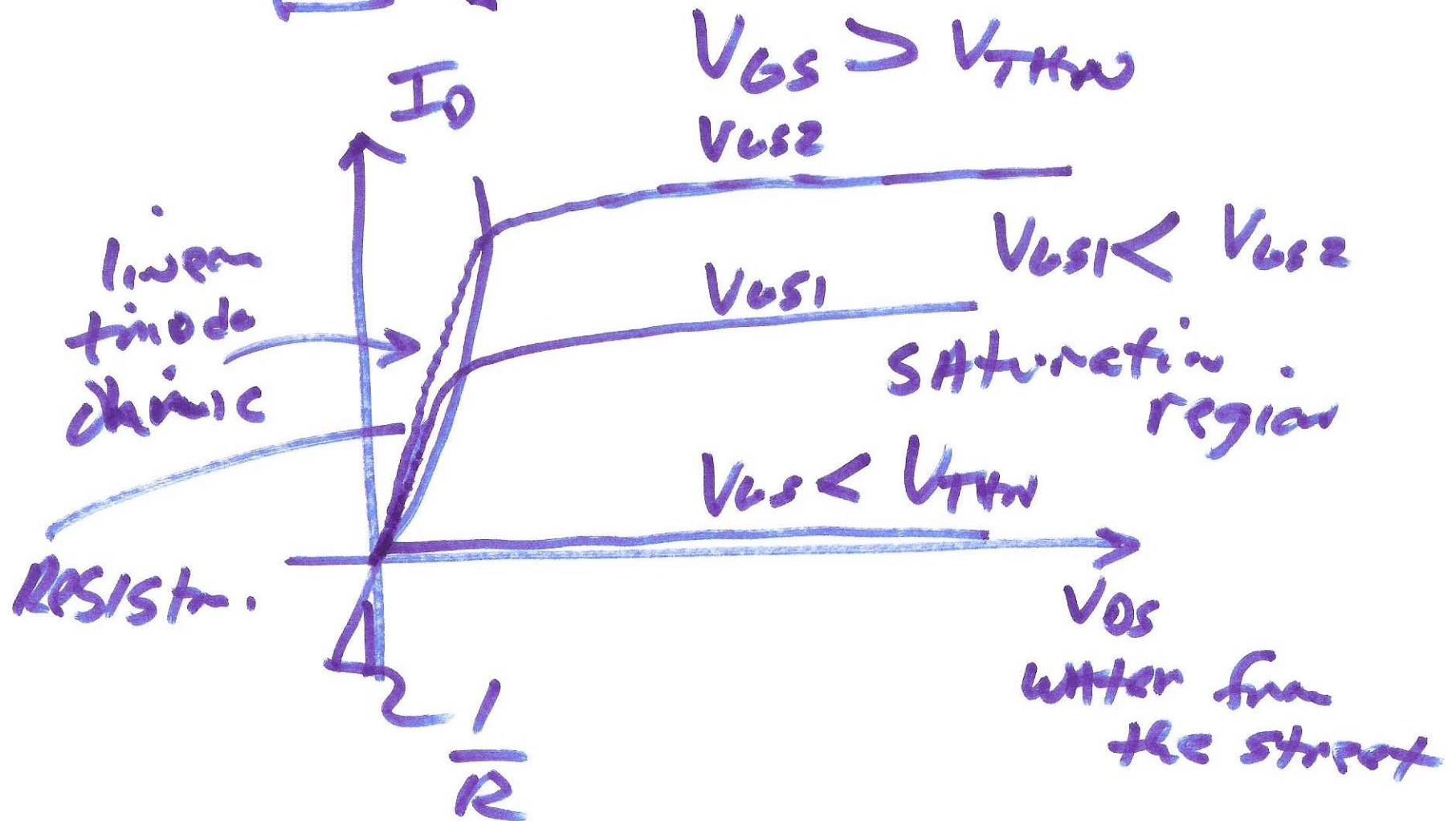
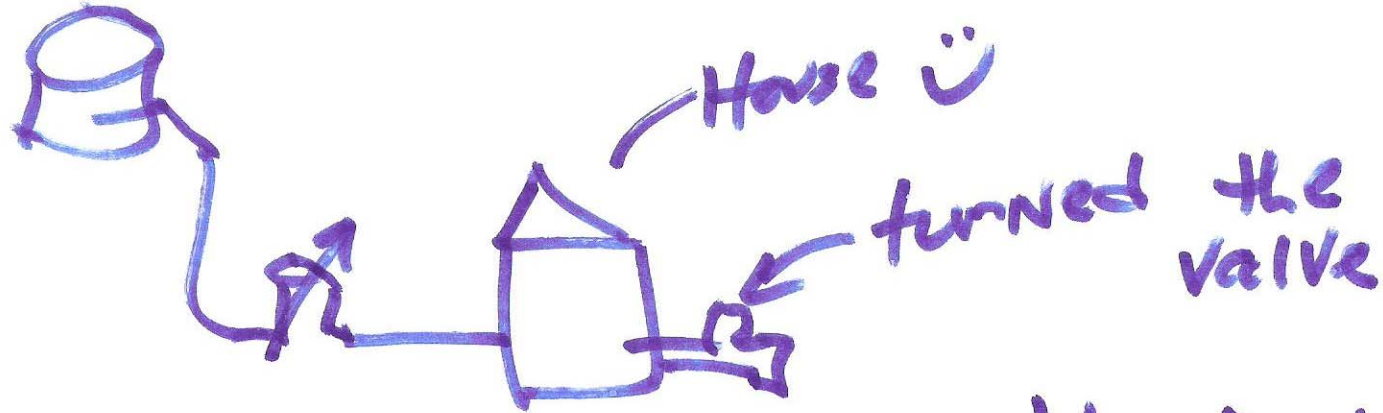
5)



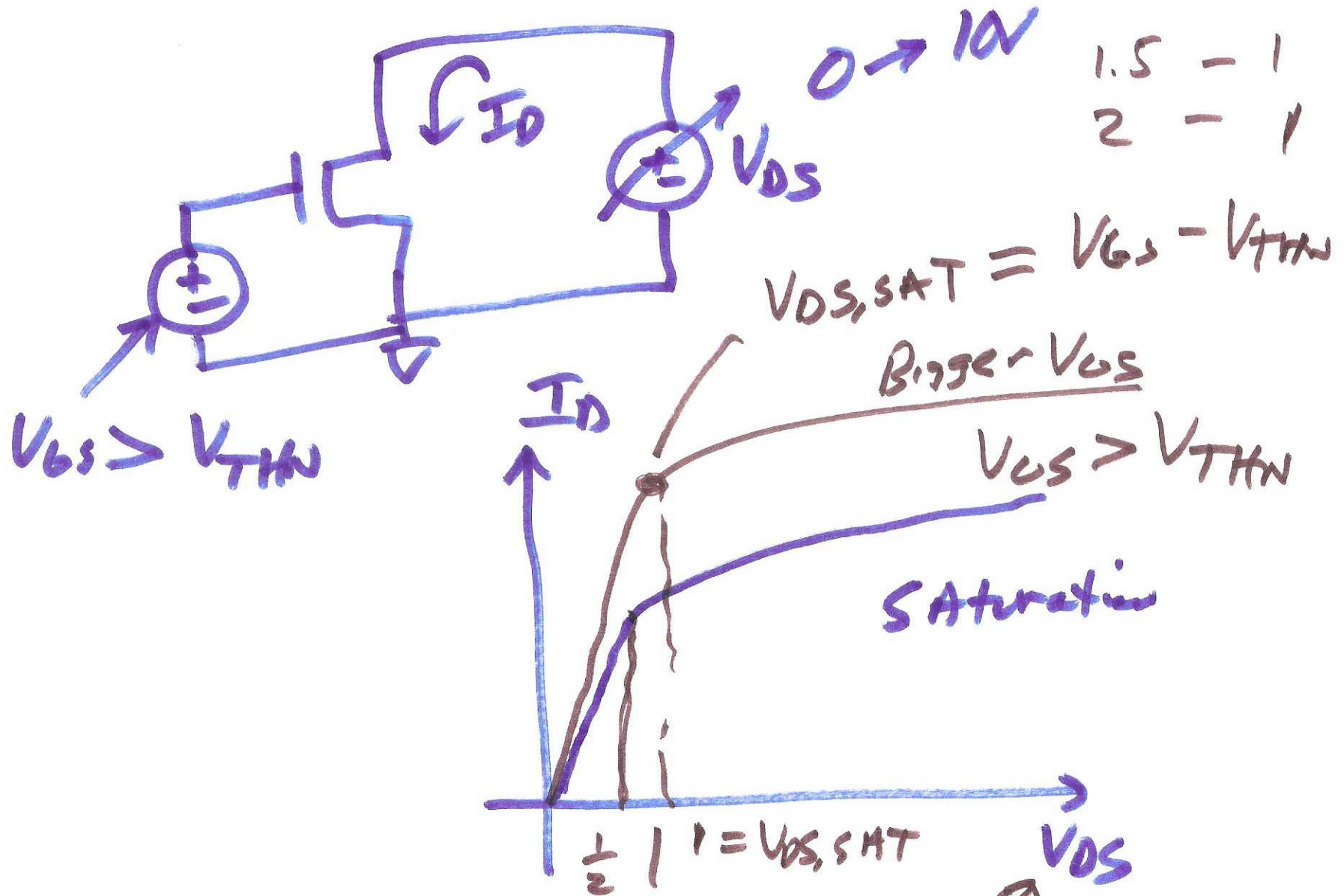
$$I_D = 0, V_{GS} \leq V_{THN}$$

$$I_D = \frac{K_N}{2} (V_{GS} - V_{THN})^2$$









8)

